

Transistor type	P _{dmx} @ 25°C Watts	I _{cmx} @ 25°C Amps.	V _{CE(sat)} volts d.c.	V _{ceo} (Sus) volts d.c.	V _{cen} (Sus) volts d.c.	V _{ces} volts d.c.	V _{eco} volts d.c.	T _j max. °C	D.C. current min	current typ.	gain max.	Small signal min.	Signal typ.	h _{ie} max.	V _{BE} max.	θ _{JA} °C/W	Derate above 25°C W/°C
2N 3055	115.5	18.0	1.1	60	70	90	7	200	20	50	70	15	50	120	1.8	1.5	0.7
ECN 055	50.0	5.0	1.0	60	55	80	5	200	25	50	100	25	75	125	1.5	3.6	0.4
ECN 149	30.0	4.0	1.0	60	40	-	8	150	30	50	110	33	80	115	1.2	4.0	0.3
ECN 100	5.0	0.7	0.8	70	65	-	6	200	60	90	280	60	90	280	0.9	35	0.05
BC 147A	0.25	0.1	0.25	50	45	-	8	125	115	180	220	125	220	280	0.9	-	-
2N 525 (PNP)	0.25	0.6	0.25	85	30	-	-	100	35	-	85	-	45	-	-	-	-
BC 147 B	0.25	0.1	0.25	50	45	50	6	125	200	290	450	240	330	500	0.9	-	-

Transistor type	h _{ie}	h _{oe}	h _{re}	θ _{JA}
BC 147 A	2.7kΩ	18μho	1.5 × 10 ⁻⁴	0.4°C/mW
2N 525 (PNP)	1.4kΩ	25μho	3.2 × 10 ⁻⁴	-
BC 147 B	4.5kΩ	30μho	2 × 10 ⁻⁴	0.4°C/mW
ECN 100	50Ω	-	-	-
ECN 149	15Ω	-	-	-
ECN 055	12Ω	-	-	-
2N 3055	6Ω	-	-	-

BFW 11-JFET MUTUAL CHARACTERISTICS

-V _{GS} volts	I _{DS} mA		-V _{DS} Volts	r _d	Derate above 25°C							
	typ.	max.										
0.0	0.2	0.4	0.8	1.0	1.2	1.6	2.0	2.4	2.5	3.0	3.5	4.0
10	9.0	8.3	7.6	6.1	5.4	4.2	3.1	2.2	2.0	1.1	0.5	0.0
7.0	6.0	5.4	4.8	4.0	3.3	2.7	1.7	0.8	0.2	0.0	0.0	0.0
4.0	3.0	2.2	1.6	1.0	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0

N-Channel JFET

Type	V _{DS} max. Volts	V _{DS} max. Volts	V _{GS} max. Volts	P _d max. @ 25°C	T _j max.	I _{DS}	g _{fs} (typical)	-V _{DS} Volts	r _d	Derate above 25°C	θ _{JA}
2N3822	50	60	50	300 mW	175°C	2 mA	3000 μ mho	6	60 kΩ	2 mW/°C	0.89°C/mW
BFW 11 (typical)	30	30	30	300 mW	200°C	7 mA	5800 μ mho	2.5	50 kΩ	-	0.81°C/mW